

An Efficient Design of 3bit and 4bit Flash ADC

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ABSTRACT

The performance of Flash Analog-to-Digital converter is greatly influenced by the choice of Comparator and **Thermometer-to- Binary encoder design**. The work describes the design and pre-simulation of a , 3bit and an 4bit analog to digital converter for low power CMOS. It requires 2^N-1 comparators, an encoder to convert thermometer code to binary code. The design is simulated in cadence environment using spectre **simulator under 90nm technology**. The pre simulation results for the design shows a low power dissipation of 87uw for the comparator and 1.05mW and 1.984mW power dissipation for 3-bit and 4-bit Flash ADC respectively. The circuit operates with an input frequency of 25MHz and 1.5V supply with a conversion time of 2.162ns and 6.182ns for 3-bit and 4-bit ADC respectively.

Keywords

Low-power, CMOS comparator, Flash ADC, Thermometer encoder.

1. INTRODUCTION

An **analog-to-digital converter (ADC)** is a device that converts the input continuous physical quantity to a digital number that represents the quantity's amplitude. The result is a sequence of digital values that have converted a continuous-time and continuous-amplitude analog signal to a discrete-time and discrete-amplitude digital signal. A direct-conversion ADC or flash ADC has a **bank of comparators sampling the input signal in parallel**, each firing for their decoded voltage range. The comparator bank feeds an encoder logic circuit that generates a code for each voltage range.

2. FLASH CONVERTER

Flash ADCs (**sometimes called parallel ADCs**) are the fastest type of ADC and use large numbers of comparators. The input signal is applied to all the comparators at once, so the thermometer output is delayed by only one comparator delay from the input, and the encoder N-bit output by only a few gate delays on top of that, so the process is very fast. An N-bit flash ADC consists of 2^N resistors and 2^N-1 comparators arranged as in Figure Fig 1. Each comparator has a reference voltage which is 1 LSB higher than that of the one below it in the chain. For a given input voltage, all the comparators below a certain point will have their input voltage larger than their reference voltage and a "1" logic output, and all the comparators above that point will have a reference voltage larger than the input voltage and a "0" logic output. The 2^N-1 comparator outputs therefore behave in a way analogous to a mercury thermometer, and the output code at this point is sometimes called a thermometer code. Since 2^N-1 data outputs are not really practical, they are processed by a decoder to generate an N-bit binary output.

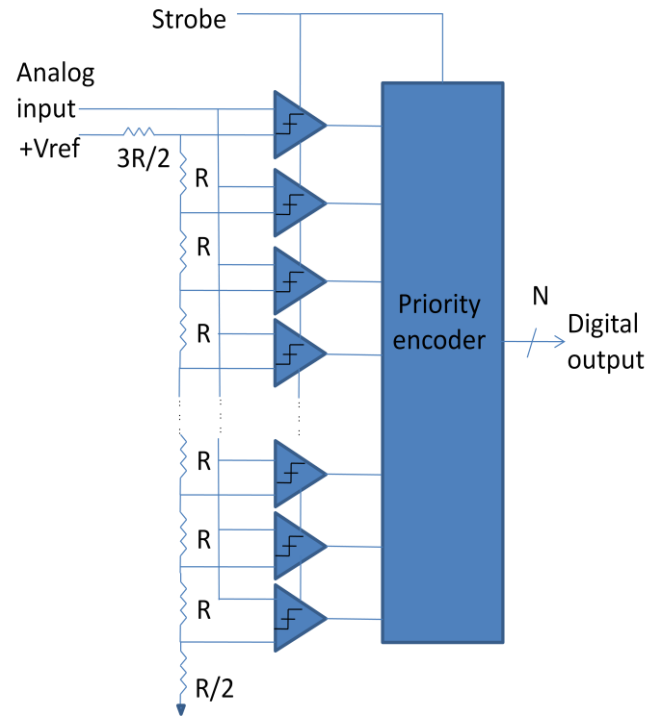


Figure 1: N-Bit Flash ADC

The architecture uses large numbers of resistors and comparators and is limited to low resolutions, and if it is to be fast, each comparator must run at relatively high power levels. Hence, the problems of flash ADCs include limited resolution, high power dissipation because of the large number of high speed comparators and relatively large (and therefore expensive) chip sizes. In addition, the resistance of the reference resistor chain must be kept low to supply adequate bias current to the fast comparators.

2.1 Comparator

The low power comparator circuit used in the design of Flash ADC is shown in fig 2 which is proposed in [1]. This circuit uses a preamplifier and a latch stage. In the preamplifier stage to achieve an acceptable gain the input differential pair uses NMOS transistors and the load uses PMOS transistors. The latch stage consists of two inverters which are connected in a back to back fashion forming a differential comparator and an NMOS transistor is connected between the two differential nodes of the latch. The design was implemented in cadence using 180nm technology [1]. In our proposed work pre-simulation results are shown using 90nm technology.

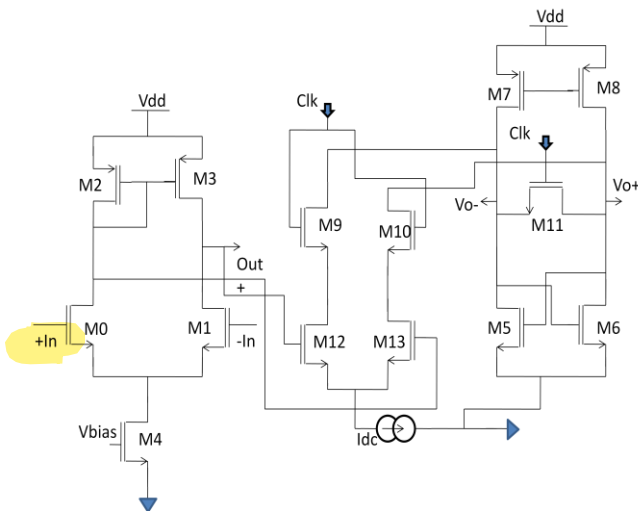


Fig 2: Preamplifier-Latch comparator

The preamplifier stage improves the sensitivity of the comparator and isolates the comparator input from switching noise of the positive feedback stage [3]. The latch stage gives the information about which of the input signals is larger and amplifies the difference between the signals [7].

2.2 Thermometer to Binary code converter

The logic encoder used for 3bit and 4bit ADC are as shown in fig 3 and fig 4. This is a multiplexer based encoder which converts thermometer codes to binary codes. Table 1 and table 2 show the truth table for 3bit and 4bit encoders. The multiplexers used are designed using transmission gates for better accuracy.

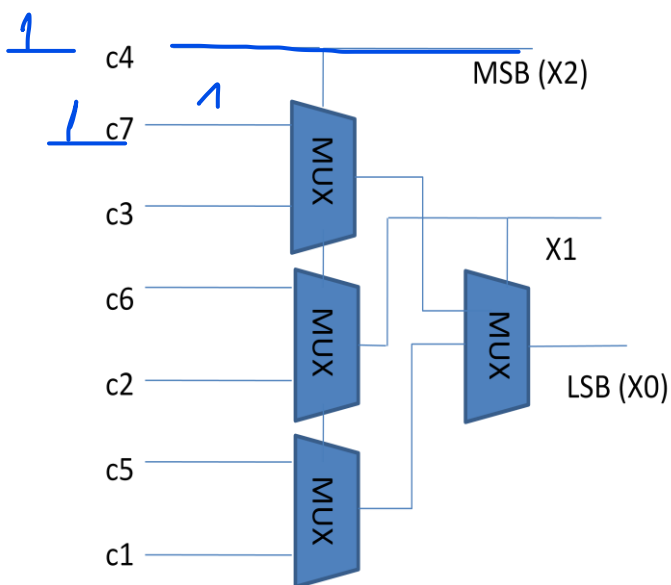


Fig 3: Logic Encoder for 3bit ADC

Table 1: Truth table for 3bit encoder

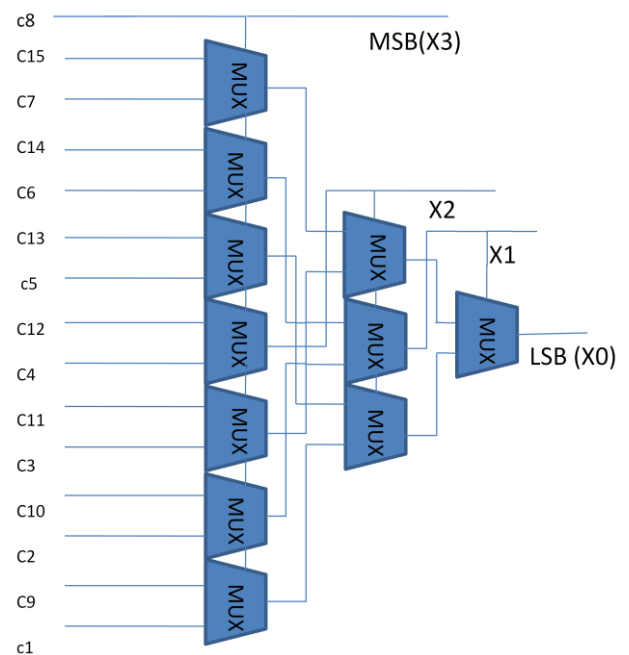
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Fig 4: Logic Encoder for 4bit ADC

Table 2: Truth table for 4bit encoder[illegible]

3. PRE SIMULATION RESULTS

3.1 Comparator output

The schematic of comparator using 90nm technology is shown in fig 4. The input signal applied to the non-inverting terminal is a sine wave and a dc reference voltage is applied to the inverting terminal of the comparator. The resulting waveform at the output of the comparator is as shown in fig 5.

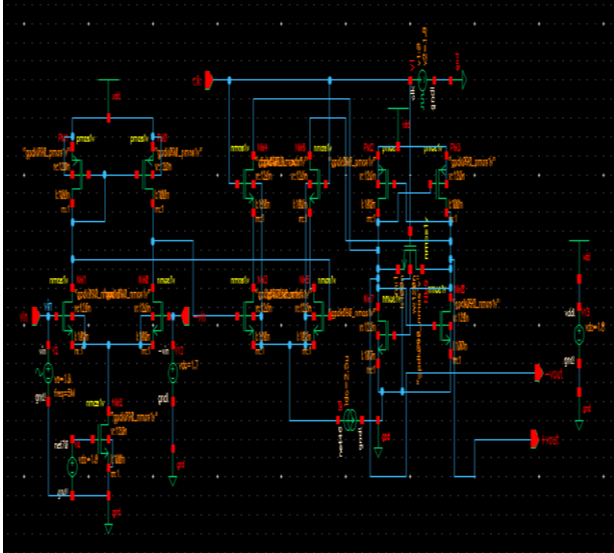


Fig 5: Schematic of comparator

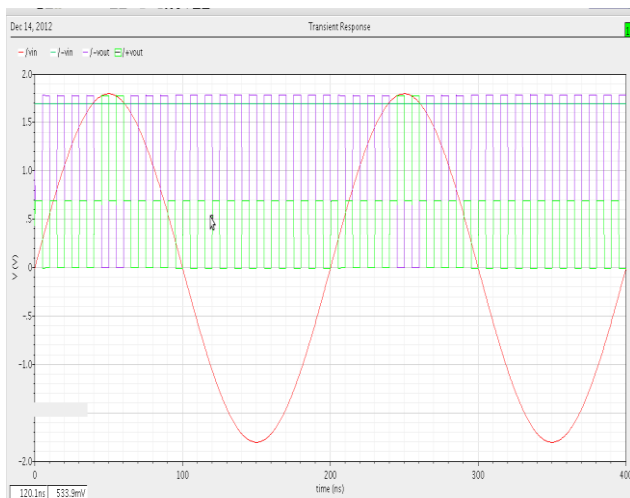


Fig 6: Comparator output waveform

3.2 Flash ADC output

The above obtained 2^N-1 comparator outputs are encoded into 3bit output and 4bit output for 3bit and 4bit ADCs respectively using an encoder and the resulting waveform of both resolution ADCs are as shown in fig 9 and fig 10. The schematic views of ADCs are shown in fig 7 and fig 8.

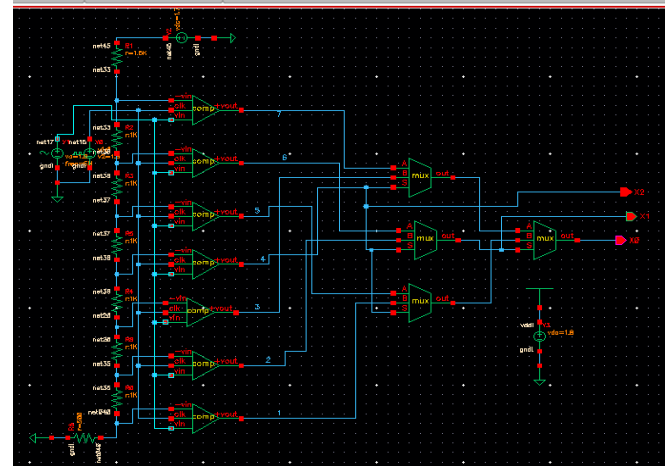


Fig 7: Schematic view of 3bit ADC

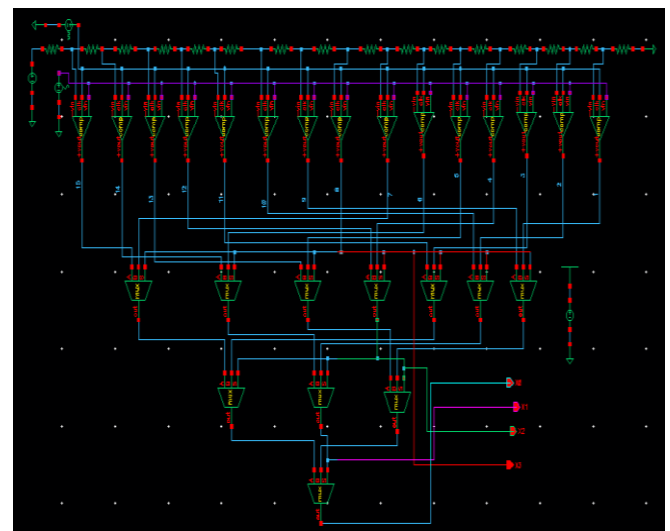


Fig 8: Schematic view of 4bit ADC

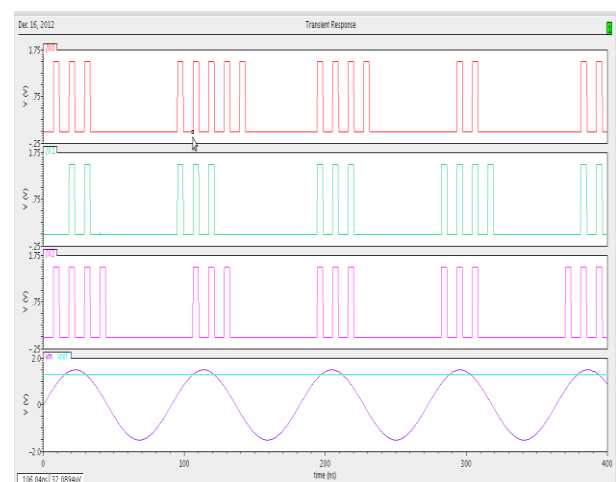


Fig 9: Output waveform of 3bit ADC

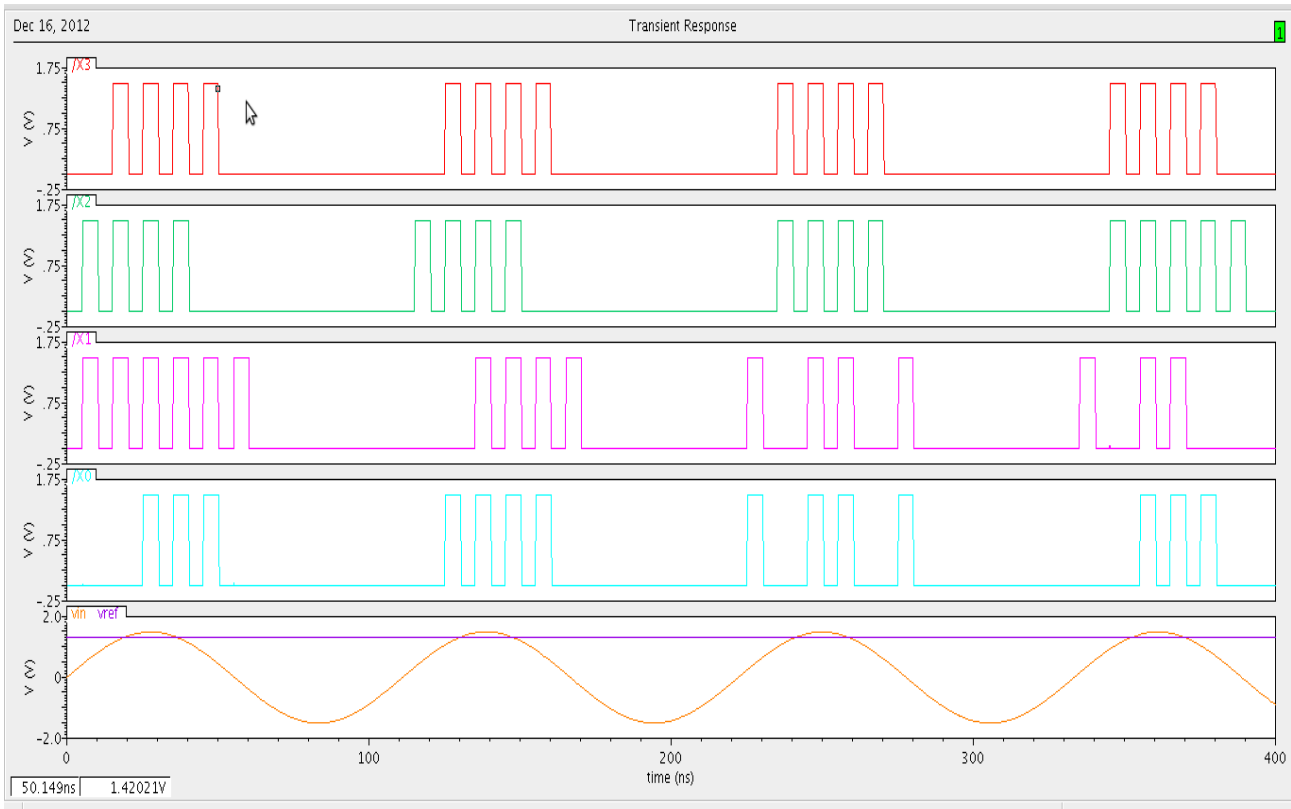


Fig 10: Output waveform of 4bit ADC

Table 3: Comparison of Present work with earlier works for comparator

References	Technology	Power dissipation	Voltage
[4]	350nm	200uW	2V
[5]	250nm	153uW	1.8V
[6]	180nm	132.7uW	2V
Proposed work	90nm	87uW	1.5V

Table 4: Comparison of Present work with earlier works for ADC

References	Technology	Resolution	Power dissipation	Voltage
[11]	350nm	6-bit	4.36mW	3.3V
Proposed work	90nm	3-bit	1.05mW	1.5V
Proposed work	90nm	4-bit	1.984mW	1.5V

Table 3 and Table 4 shows the parameter values obtained for the comparator and 4bit ADC circuit under 90nm technology with supply voltage equal to 1.5V.

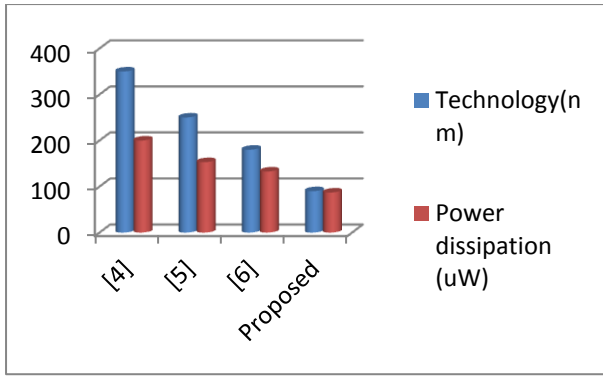


Fig 11: Comparison of Comparator results between earlier and proposed work

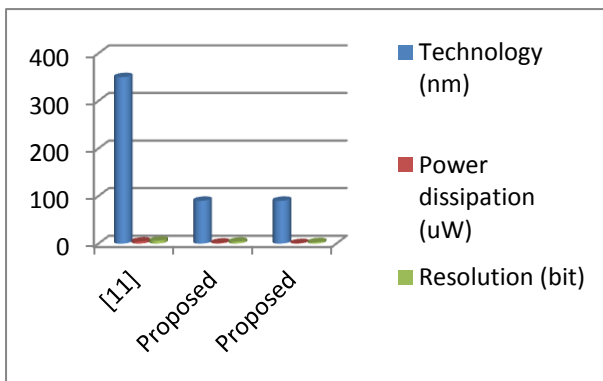


Fig 12: Comparison of ADC results between earlier and proposed work

Comparison between earlier work and proposed work for comparator and ADC results are shown in Fig 11 and Fig 12.

4 CONCLUSIONS

The problem of flash ADCs lies with limited resolution, high power dissipation because of the large number of high speed comparator. In this regard an attempt is made to design low-power 3bit and 4bit ADCs. The design and Pre simulation are carried out in cadence environment using spectre simulator under 90nm technology. The pre simulation results for the design shows a low power dissipation of 87uW for the comparator and 1.05mW and 1.984mW power dissipation for 3-bit and 4-bit Flash ADC respectively. The circuit operates with an input frequency of 25MHz and 1.5V supply with a conversion time of 2.162ns and 6.182ns for 3-bit and 4-bit ADC respectively. The ADC design can be used for low power and high speed applications. The proposed architecture can be extended to higher resolution. For the proposed architecture area optimization must be done in the future.

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